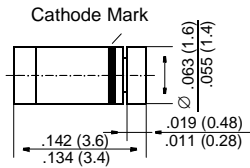


# BAV100 THRU BAV103

## Small Signal Diodes

### MiniMELF



Dimensions in inches and (millimeters)

### FEATURES

- ◆ Silicon Epitaxial Planar Diodes
- ◆ For general purpose
- ◆ These diodes are also available in other case styles including: the DO-35 case with the type designations BAV19 to BAV21, the SOD-123 case with the type designations BAV19W to BAV21W, and the SOT-23 case with the type designation BAS19 - BAS21.



### MECHANICAL DATA

**Case:** MiniMELF Glass Case (SOD-80)

**Weight:** approx. 0.05 g

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Reverse Voltage <b>BAV100</b> <b>BAV101</b> <b>BAV102</b> <b>BAV103</b>	$V_R$ $V_R$ $V_R$ $V_R$	60 120 200 250	V V V V
Forward DC Current at $T_{amb} = 25\text{ °C}$	$I_F$	250 <sup>1)</sup>	mA
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25\text{ °C}$ and $f \geq 50\text{ Hz}$	$I_0$	200 <sup>1)</sup>	mA
Repetitive Peak Forward Current at $f \geq 50\text{ Hz}$ , $\Theta = 180\text{ °C}$ , $T_{amb} = 25\text{ °C}$	$I_{FRM}$	625 <sup>1)</sup>	mA
Surge Forward Current at $t < 1\text{ s}$ , $T_j = 25\text{ °C}$	$I_{FSM}$	1	A
Power Dissipation at $T_{amb} = 25\text{ °C}$	$P_{tot}$	400 <sup>1)</sup>	mW
Junction Temperature	$T_j$	175	°C
Storage Temperature Range	$T_S$	-65 to +175	°C

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.

# BAV100 THRU BAV103

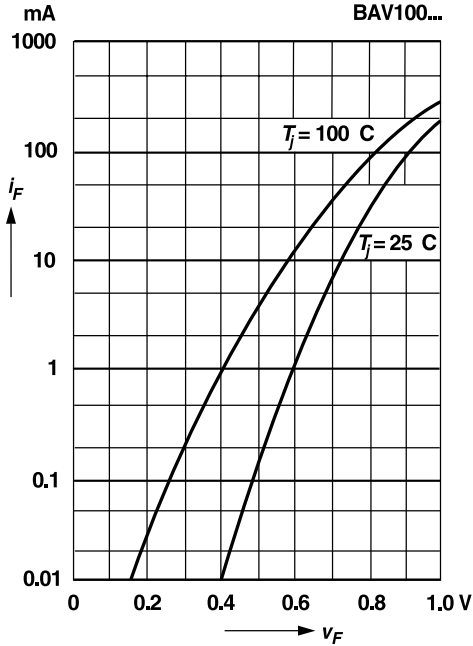
## ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Forward voltage at $I_F = 100 \text{ mA}$	$V_F$	–	–	1	V
Leakage Current at $V_R = 50 \text{ V}$	<b>BAV100</b> $I_R$	–	–	100	nA
at $V_R = 50 \text{ V}, T_j = 100 \text{ °C}$	<b>BAV100</b> $I_R$	–	–	15	$\mu\text{A}$
at $V_R = 100 \text{ V}$	<b>BAV101</b> $I_R$	–	–	100	nA
at $V_R = 100 \text{ V}, T_j = 100 \text{ °C}$	<b>BAV101</b> $I_R$	–	–	15	$\mu\text{A}$
at $V_R = 150 \text{ V}$	<b>BAV102</b> $I_R$	–	–	100	nA
at $V_R = 150 \text{ V}, T_j = 100 \text{ °C}$	<b>BAV102</b> $I_R$	–	–	15	$\mu\text{A}$
at $V_R = 200 \text{ V}$	<b>BAV103</b> $I_R$	–	–	100	nA
at $V_R = 200 \text{ V}, T_j = 100 \text{ °C}$	<b>BAV103</b> $I_R$	–	–	15	$\mu\text{A}$
Dynamic Forward Resistance at $I_F = 10 \text{ mA}$	$r_f$	–	5	–	$\Omega$
Capacitance at $V_R = 0, f = 1 \text{ MHz}$	$C_{\text{tot}}$	–	1.5	–	pF
Reverse Recovery Time from $I_F = 30 \text{ mA}$ through $I_R = 30 \text{ mA}$ to $I_R = 3 \text{ mA}; R_L = 100 \Omega$	$t_{\text{rr}}$	–	–	50	ns
Thermal Resistance Junction to Ambient Air	$R_{\text{thJA}}$	–	–	0.375 <sup>1)</sup>	K/mW
1) Valid provided that electrodes are kept at ambient temperature.					

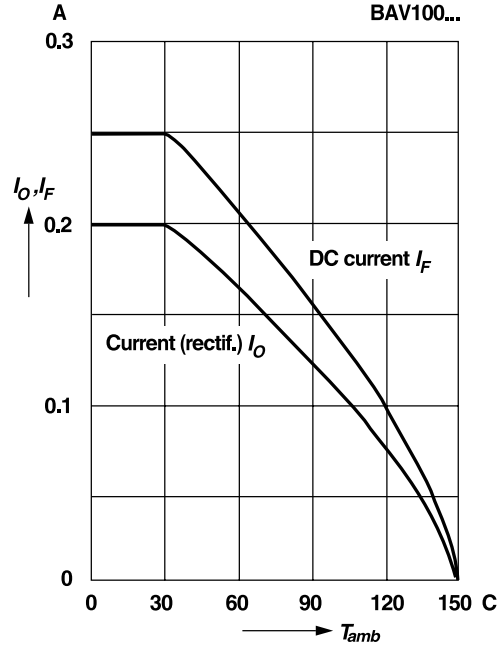
# RATINGS AND CHARACTERISTIC CURVES BAV100 THRU BAV103

Forward characteristics



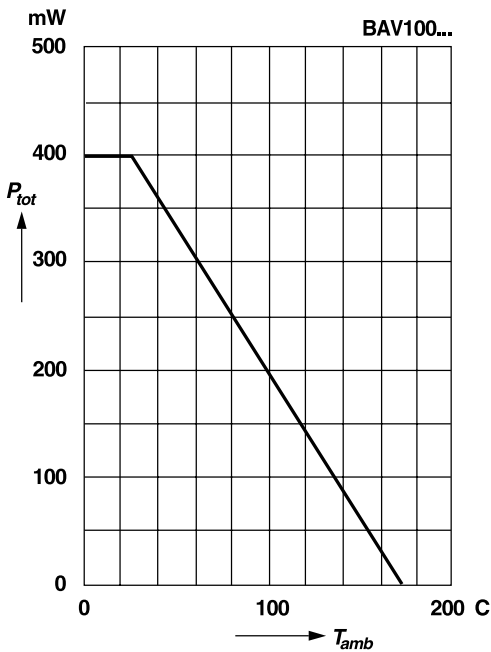
Admissible forward current versus ambient temperature

Valid provided that electrodes are kept at ambient temperature

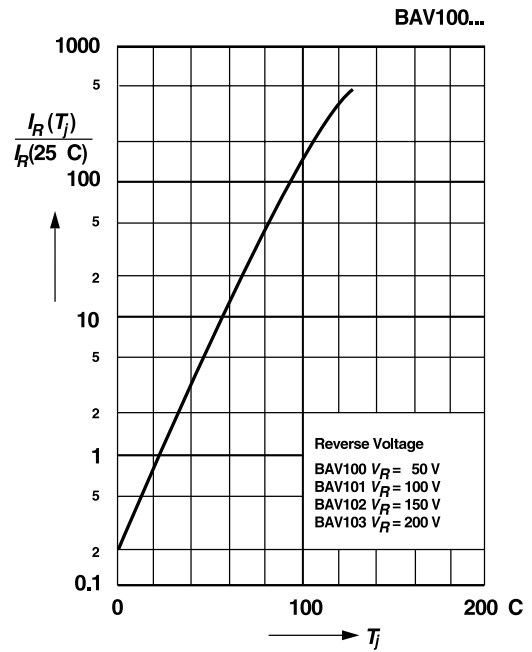


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature

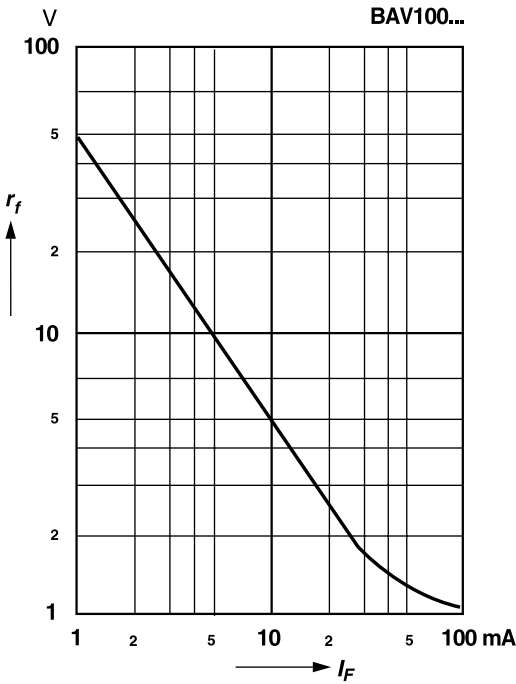


Leakage current versus junction temperature



# RATINGS AND CHARACTERISTIC CURVES BAV100 THRU BAV103

**Dynamic forward resistance  
versus forward current**



**Capacitance  
versus reverse voltage**

